IN THE CLAIMS

- 1 (Previously Presented). A method comprising:

 forming a substantially crystalline, non-switching ovonic material; and
 forming a phase change material that changes between more conductive and less
 conductive states coupled to said non-switching ovonic material.
- 2 (Original). The method of claim 1 including forming said non-switching ovonic material over said phase change material and forming a second ovonic material under said phase change material.
- 3 (Original). The method of claim 1 including contacting said non-switching ovonic material with an electrode.
- 4 (Original). The method of claim 3 including forming a second ovonic material over said phase change material, forming said non-switching ovonic material under said phase change material, and contacting said non-switching and second ovonic materials with electrodes.
- 5 (Original). The method of claim 1 including forming said phase change material and said non-switching ovonic material in a pore formed in an insulator.
- 6 (Original). The method of claim 1 including forming a second ovonic material in a cupshape over said phase change material.
- 7 (Original). The method of claim 6 including filling said cup-shaped ovonic material with an insulator.
- 8 (Original). The method of claim 7 including covering said phase change material with an insulating material.

- 9 (Original). The method of claim 8 including positioning said second ovonic material on a portion of said phase change material and covering the rest of said phase change material with nitride.
- 10 (Original). The method of claim 1 including forming a cup-shaped first ovonic material and forming said phase change material within said cup-shaped first ovonic material.
- 11 (Original). The method of claim 10 including providing a second ovonic material that contacts the upper side of said phase change material.
- 12 (Previously Presented). The method of claim 11 including covering a portion of said phase change material with an insulator and causing said second ovonic material to contact only a portion of said first phase change material.
- 13 (Original). The method of claim 10 wherein said non-switching ovonic material is a stable structural phase.
 - 14 (Previously Presented). A memory comprising:
 - a substantially crystalline, non-switching ovonic material; and
- a phase change material that changes between more conductive and less conductive states coupled to said non-switching ovonic material.
- 15 (Original). The memory of claim 14 including a second ovonic material over said phase change material.
- 16 (Original). The memory of claim 14 including an electrode contacting said non-switching ovonic material.
- 17 (Original). The memory of claim 15 including a first electrode contacting said non-switching ovonic material and a second electrode contacting said second ovonic material, said phase change material sandwiched between said non-switching ovonic material, said second

ovonic material, and said first and second electrodes, and said phase change material being sandwiched by said first and second electrodes.

- 18 (Original). The memory of claim 14 including a substrate under said first ovonic material.
- 19 (Original). The memory of claim 14 wherein said non-switching ovonic material is cupshaped.
- 20 (Original). The memory of claim 19 wherein said phase change material is in said cupshaped non-switching ovonic material.
- 21 (Original). The memory of claim 14 including a second ovonic material over said phase change material, said second ovonic material being cup-shaped.
- 22 (Original). The memory of claim 21 including an insulator in said cup-shaped second ovonic material.
- 23 (Original). The memory of claim 21 wherein said second ovonic material is in contact with said phase change material along a portion of the phase change material and the remaining portion of said phase change material is covered by an insulator.
- 24 (Original). The memory of claim 14 wherein said non-switching ovonic material is a chalcogenide.
- 25 (Previously Presented). The memory of claim 14 wherein said phase change material is a chalcogenide.
- 26 (Original). The memory of claim 14 wherein said non-switching ovonic material and said phase change material are formed of a chalcogenide.

- 27 (Previously Presented). A system comprising:
 - a processor-based device;
 - a wireless interface coupled to said processor-based device; and
- a semiconductor memory coupled to said device, said memory including a substantially crystalline, non-switching ovonic material and a phase change material that changes between more conductive and less conductive states over said non-switching ovonic material.
- 28 (Original). The system of claim 27 wherein said wireless interface includes a dipole antenna.
- 29 (Original). The system of claim 27 wherein said non-switching ovonic material and said phase change material are both formed of a chalcogenide.
- 30 (Original). The system of claim 27 including a second ovonic material over said phase change material.